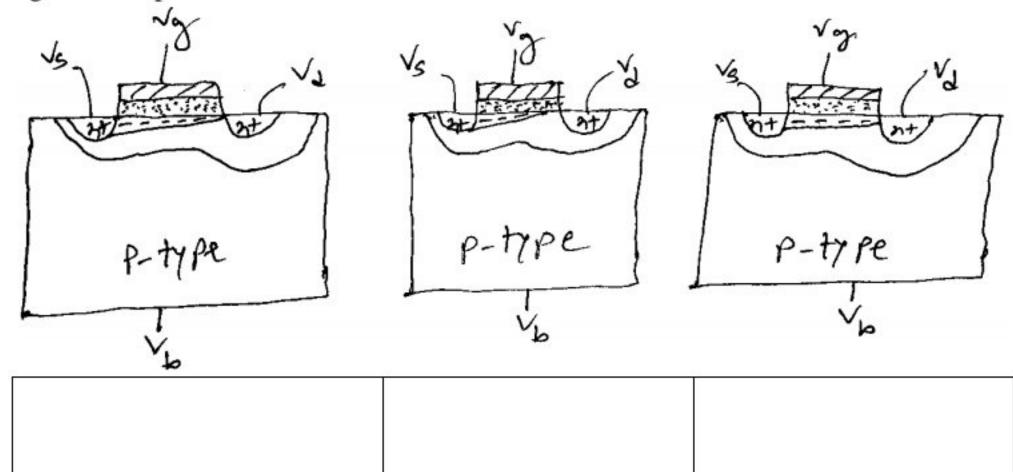
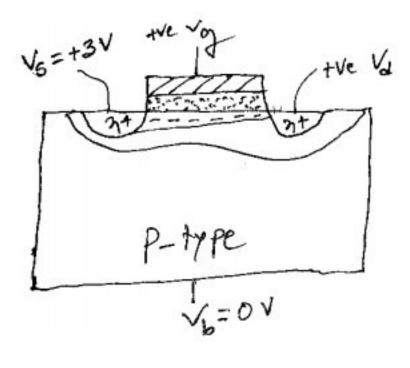
Q1. Mention the working state of each of the MOSFET in the blank box beneath each of the 3 figures. Be specific.



Q2. Draw the typical I_{ds} versus V_{ds} characteristics curve of an enhancement mode NMOS 4 for a constant V_{gs} .

Q3. Determine the threshold voltage of the following NMOS considering the body-effect 5 where initial threshold is 0.8V. Consider that except the necessary parameters all others are constant.



Solution:

Q4. Consider an enhancement mode NMOS where W:L=1:1. The gate input is 2V; source, 8 drain, and body are connected to 1V, 2V, and 0V respectively, and threshold is 1V. Now determine the current through the NMOS. (You can use opposite page if necessary).

Marks: 20

Course No.: CSE 4207

CT#3

Time: 25 Minutes

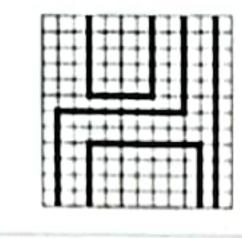
Marks: 20

Q1. For a CMOS inverter $W_1:L_1=1:1$, $W_2:L_2=2:1$, $V_{te}=V_{tep}=1V$, $\frac{\epsilon\mu_n}{D}=3x10^{-8}\frac{mA}{mV^2}$, $14\frac{\epsilon\mu_p}{2D}=0.75x10^{-11}\frac{A}{mV^2}$. Now if $V_{sg}=V_{gs}=3.3V$ then find out the followings (a-d) for both load and driver transistors: (You must specify the necessary equations clearly).

- a. Pinch-off voltages
- b. Input voltages
- c. Output voltages
- d. Saturation currents
- e. Finally find out the current flow throughout the CMOS inverter.

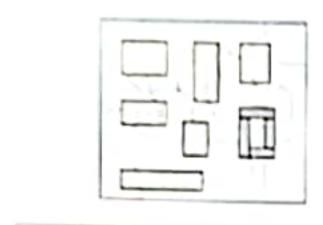
Q2. Briefly explain the operating principle of CMOS transmission gate with necessary 6 diagram.

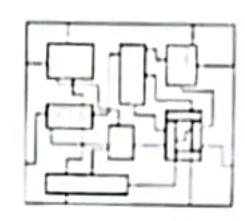
Q1 Mention the name of each of the routing models beneath the individual figures.



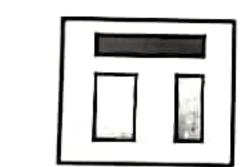


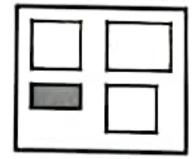
Q2. Mention the name of each of the routing technique used beneath the individual figures. 4

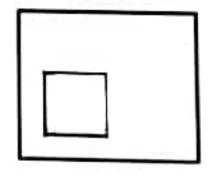




Q3. Mention the name of each of the channel junction created beneath the individual 6 figures.







Q4 Mention the name of each of the routing regions created beneath the individual 6 figures.



